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Should be replaced with:

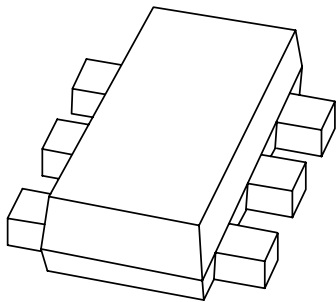
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Kind regards,

Team Nexperia

DATA SHEET



PEMZ1 NPN/PNP general purpose transistors

Product data sheet
Supersedes data of 2001 Sep 25

2001 Nov 07

NPN/PNP general purpose transistors

PEMZ1

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Complementary MOSFET driver for switch mode power supply
- Complementary driver for audio amplifiers.

DESCRIPTION

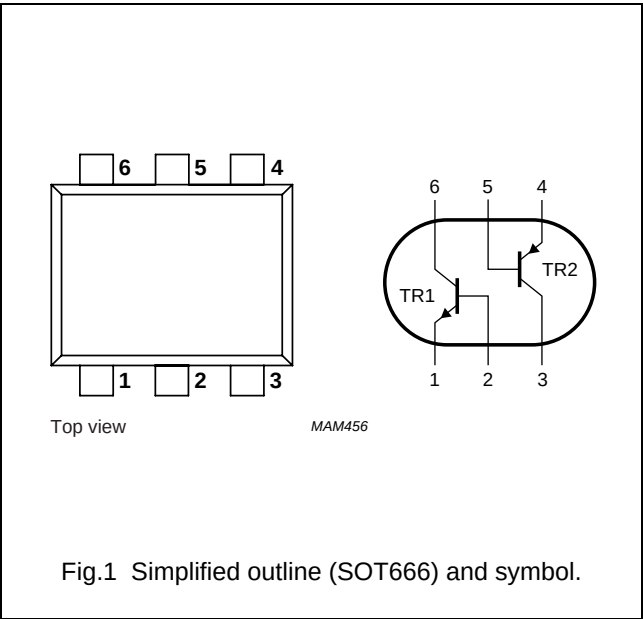
NPN/PNP transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PEMZ1	FZ

PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base	–	40	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	100	mA
I _{CM}	peak collector current		–	200	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$; unless otherwise specified.

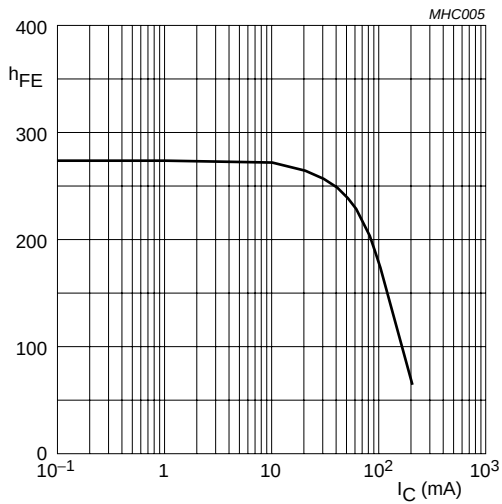
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity						
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 30\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	10	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\text{ V}; I_C = 0$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 6\text{ V}; I_C = 1\text{ mA}$	120	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 50\text{ mA}; I_B = 5.0\text{ mA}; \text{note 1}$	–	–	200	mV
f_T	transition frequency	$I_C = 2\text{ mA}; V_{CE} = 12\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
C_c	collector capacitance	$I_E = I_E = 0; V_{CB} = 12\text{ V}; f = 1\text{ MHz}$				
	TR1 (NPN)		–	–	1.5	pF
	TR2 (PNP)		–	–	2.2	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

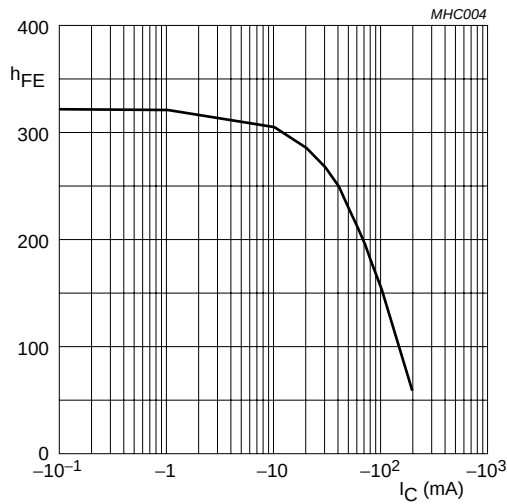
NPN/PNP general purpose transistors

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TR1 (NPN); $V_{CE} = 5$ V.

Fig.2 DC current gain as a function of collector current; typical values



TR2 (PNP); $V_{CE} = -5$ V.

Fig.3 DC current gain as a function of collector current; typical values

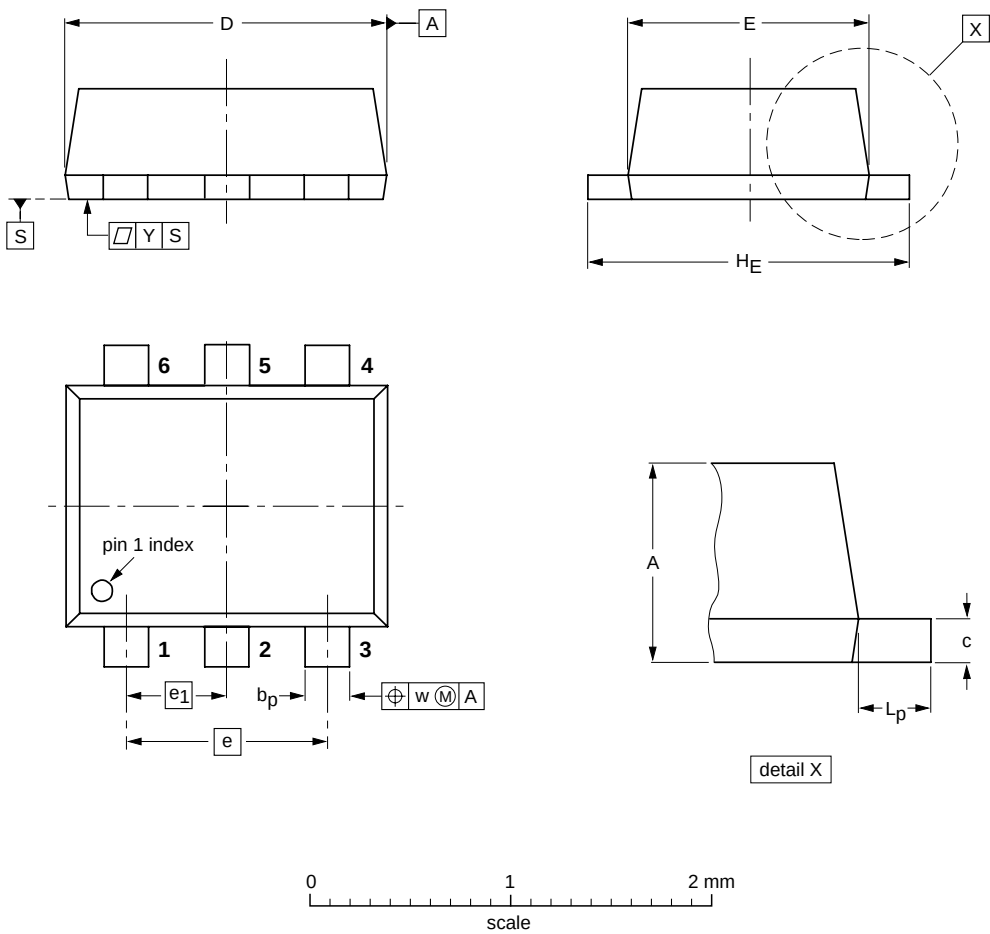
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PACKAGE OUTLINE

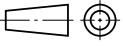
Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT666						01-01-04 01-08-27

NPN/PNP general purpose transistors

PEMZ1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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For additional information please visit: **<http://www.nxp.com>**

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